

Substitute form 1449A/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/849,589
		Filing Date	May 20, 2004
		First Named Inventor	Adam Saxler
		Group Art Unit	2814
		Examiner Name	Wael M. Fahmy John C. Ingham
Sheet 1 of 1	Attorney Docket Number	5308-412	

U.S. PATENTS AND PATENT PUBLICATIONS

Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
9CI	1.	US-5,990,531		Taskar et al.	11-23-1999
9CI	2.	US-5,389,571		Takeuchi et al.	02-14-1995
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OTHER NON PATENT LITERATURE DOCUMENTS

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Examiner Signature	<i>John C. Ingham</i>	Date Considered	10/24/05
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Sheet

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13

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First Named Inventor

Adam Saxler

Group Art Unit

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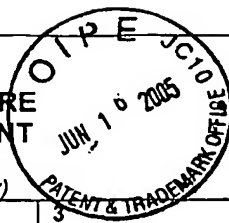
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of

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9ci	11.	JP	11261053		Furukawa Electric Co. Ltd.	05-24-1999	Abstract
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9ci	37.	United States Patent Application entitled "High Power Density and/or Linearity Transistors," Serial No. 11/005,107, filed December 6, 2004 (Attorney Docket No. 5308-511).		
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9ci	40.	United States Patent Application entitled "Aluminum Free Group III-Nitride Based High Electron Mobility Transistors and Methods of Fabricating Same," Serial No. 11/118,575, filed April 29, 2005 (Attorney Docket No. 5308-543).		
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		First Named Inventor	Saxler
		Group Art Unit	2814
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9ci	42.	United States Patent Application entitled "Composite Substrates of Conductive And Insulating or Semi-Insulating Group III-Nitrides For Group III-Nitride Devices," Serial No. 11/103,127, filed April 11, 2005 (Attorney Docket No. 5308-551).	
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Examiner Signature	<i>John Ingham</i>	Date Considered	10/24/05
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Form PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Attorney Docket No. 5308-412		Serial No. 10/849,589	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicant: Saxler			
				Filing Date: May 20, 2004		GAU-2811-2814	
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Examiner Initials		Document No.	Date (m/d/y)	Name	Class	Subclass	Filing Date if Appropriate
9cl	1.	5,592,501	1/7/97	Edmond et al.	372	45	
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		Document Number	Date	Country	Class	Subclass	Translation (Yes/No)
OTHER DOCUMENTS							

Examiner:

John J. Smith

Date Considered:

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Group Art Unit	2011 2814
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Examiner Name	Wael M. Fahmy
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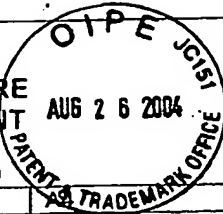
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9CI	73.	Ben-Yaacov et al., "AlGaIn/GaN Current Aperture Vertical Electron Transistors with Regrown Channels," <i>Journal of Applied Physics</i> . Vol. 95, No. 4, pp. 2073-2078 (2004).			
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9CI	80.	Egawa et al. "Recessed gate AlGaIn/GaN MODFET on Sapphire Grown by MOCVD," <i>Applied Physics Letters</i> . Vol. 76, No. 1, pp. 121-123 (January 2000).			
9CI	81.	Gaska et al. "High-Temperature Performance of AlGaIn/GaN HFET's on SiC Substrates," <i>IEEE Electron Device Letters</i> . Vol. 18, No. 1, pp. 492-494 (October 1997).			
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9CI	83.	Gelmont et al. "Monte Carlo simulation of electron transport in gallium nitride," <i>Journal of Applied Physics</i> . Vol. 74, No. 3, pp. 1818-1821 (August 1993).			

Examiner Signature	<i>John Ingham</i>	Date Considered	10/24/05
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Substitute form 1449A/PTO		Complete if Known			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/849,589		
		Filing Date	May 20, 2004		
		First Named Inventor	Saxler		
		Group Art Unit	2811-2814		
		Examiner Name	Waet M. Fahmy John Ingham		
Sheet	A3	of	A4	Attorney Docket Number	5308-412

OTHER NON PATENT LITERATURE DOCUMENTS				
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9ci	84.	Gradecak, "Microscopic Evidence of Point Defect Incorporation in Laterally Overgrown GaN," <i>Applied Physics Letters</i> . Vol. 80, No. 16, pp. 2866-2868 (2002).		
9ci	85.	Heikman, et al., "Mass Transport Regrowth of GaN for Ohmic Contacts to AlGaIn/GaN," <i>Applied Physics Letters</i> . Vol. 78, No. 19, pp. 2876		
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9ci	87.	Heikman et al., "Growth of Fe-Doped Semi-insulating GaN by Metalorganic Chemical Vapor Deposition," <i>Applied Physics Letters</i> . Vol. 83, No. 1, pp. 439-441 (July 2002).		
9ci	88.	Heikman, Sten J., <i>MOCVD Growth Technologies for Applications in AlGaIn/GaN High Electron Mobility Transistors</i> , Dissertation, University of California—Santa Barbara, September 2002, 190 pages.		
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9ci	92.	Kuzmik et al. "Annealing of Schottky contacts deposited on dry etched AlGaIn/GaN," <i>Semiconductor Science and Technology</i> . Vol. 17, No. 11 (November 2002).		
9ci	93.	Neuburger et al. "Design of GaN-based Field Effect Transistor Structures based on Doping Screening of Polarization Fields," WA 1.5, 7 th Wide-Gandgap III-Nitride Workshop (March 2002).		
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9ci	95.	Sheppard et al. "High Power Demonstration at 10 GHz with GaN/AlGaIn HEMT Hybrid Amplifiers." Presented at the 58 th DRC, Denver, CO, June 2000.		
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9ci	104.	Yu et al. "Schottky barrier engineering in III-V nitrides via the piezoelectric effect," <i>Applied Physics Letters</i> . Vol. 73, No. 13, pp. 1880-1882, (September 1998).		
9ci	105.	United States Patent Application entitled "Co-Doping for Fermi Level Control in Semi-Insulating Group III Nitrides," filed January 7, 2004 (Attorney Docket No. 5308-371).		
9ci	106.	United States Patent Application entitled "Nitride Heterojunction Transistors Having Charge-Transfer Induced Energy Barriers and Methods of Fabricating the Same," Serial No. 10/772,882, filed February 5, 2004 (Attorney Docket No. 5308-389.)		
9ci	107.	United States Patent Application entitled "Nitride-Based Transistors with a Protective Layer and a Low-Damage Recess and Methods of Fabrication Thereof," Serial No. 10/758,871, filed January 16, 2004 (Attorney Docket No. 5308-291).		
9ci	108.	United States Patent Application entitled "Methods of Fabricating Nitride-Based Transistors with a Cap Layer and a Recessed Gate," filed July 23, 2004 (Attorney Docket No. 5308-392).		

Examiner Signature	<i>John Ingham</i>	Date Considered	10/24/05
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		Filing Date	May 20, 2004		
		First Named Inventor	Saxler		
		Group Art Unit	2811 2814		
		Examiner Name	Wael M. Fahmy John Ingham		
Sheet	A4	of	A4	Attorney Docket Number	5308-412

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ACI	109.	United States Patent Application entitled "Nitride-Based Transistors and Methods of Fabrication Thereof Using Non-Etched Contact Recesses," Serial No. 10/617,843, filed July 11, 2003 (Attorney Docket No. 5308-248).	
ACI	110.	United States Patent Application entitled "Methods of Having Laterally Grown Active Region and Methods of Fabricating Same," filed July 26, 2004 (Attorney Docket No. 5308-374).	
ACI	111.	United States Patent Application entitled "Methods of Fabricating Nitride-Based Transistors Having Regrown Ohmic Contact Regions and Nitride-Based Transistors Having Regrown Ohmic Contact Regions," Serial No. 10/849,617, filed May 20, 2004 (Attorney Docket No. 5308-413)	
ACI	112.	United States Patent Application entitled, "Silicon Carbide on Diamond Substrates and Related Devices and Methods," (Cree Docket No. P0387).	

Examiner Signature	<i>John Ingham</i>	Date Considered	12/24/05
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